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30A, 35V - 150V Schottky Barrier Rectifier

FEATURES

TAIWAN

• AEC-Q101 qualified available

EMICONDUCTOR

- Low power loss, high efficiency
- Guard ring for overvoltage protection
- High surge current capability
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

APPLICATIONS

- Switching mode power supply (SMPS)
- Adapters
- DC to DC converters

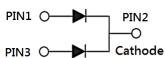
MECHANICAL DATA

- Case: TO-220AB
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Mounting torque: 0.56 N·m maximum
- Meet JESD 201 class 2 whisker test
- Polarity: As marked
- Weight: 1.90g (approximately)

| KEY PARAMETERS | | | | |
|--------------------|-----------|------|--|--|
| PARAMETER | VALUE | UNIT | | |
| I _F | 30 | А | | |
| V _{RRM} | 35 - 150 | V | | |
| I _{FSM} | 200 | А | | |
| T _{J MAX} | 150 | °C | | |
| Package | TO-220AB | | | |
| Configuration | Dual dies | | | |







| ABSOLUTE MAXIMUM RATIN | | | 1 | [| r i | MDD | MDD | MDD | |
|--|---------------------|------|------|------|-----------|------|-------|-------|-------|
| | | MBR | MBR | MBR | MBR | MBR | MBR | MBR | |
| PARAMETER | SYMBOL | 3035 | 3045 | 3050 | 3060 | 3090 | 30100 | 30150 | UNIT |
| | | СТ | СТ | СТ | СТ | СТ | СТ | СТ | |
| | | MBR | MBR | MBR | MBR | MBR | MBR | MBR | |
| Marking code on the device | | 3035 | 3045 | 3050 | 3060 | 3090 | 30100 | 30150 | |
| - | | СТ | СТ | СТ | СТ | СТ | СТ | СТ | |
| Repetitive peak reverse voltage | V_{RRM} | 35 | 45 | 50 | 60 | 90 | 100 | 150 | V |
| Reverse voltage, total rms value | V _{R(RMS)} | 24 | 31 | 35 | 42 | 63 | 70 | 105 | V |
| Forward current | I _F | | | | 30 | | | | А |
| Surge peak forward current, | | | | | | | | | |
| 8.3ms single half sine wave | I _{FSM} | | | | 200 | | | | Α |
| superimposed on rated load | - | | | | | | | | |
| Peak repetitive reverse | 1 | | 1 | | | 0 | - | | |
| surge current ⁽¹⁾ | I _{RRM} | | 1 | | | 0 | .5 | | A |
| Peak repetitive forward current | - | | | | 20 | | | | ^ |
| (Rated \dot{V}_{R} , Square wave, 20KHz) | I _{FRM} | | | | 30 | | | | A |
| Critical rate of rise of off-state | -l/ -l.t. | | | | 40.000 | | | | Maria |
| voltage | dv/dt | | | | 10,000 | | | | V/µs |
| Junction temperature | Τ _J | | | -5 | 55 to +15 | 0 | | | °C |
| Storage temperature | T _{STG} | | | -5 | 55 to +15 | 0 | | | °C |

Notes:

1. tp = 2.0µs, 1.0KHz



| THERMAL PERFORMANCE | | | | |
|-------------------------------------|--|------------------|-----|------|
| PARAMETER | | SYMBOL | ТҮР | UNIT |
| Junction-to-case thermal resistance | MBR3035CT MBR3045CT MBR3050CT MBR3060CT | R _{ejc} | 1.0 | °C/W |
| Junction-to-case thermal resistance | MBR3090CT MBR30100CT MBR30150CT | R _{ejc} | 1.5 | °C/W |

| ELECTRICAL SPECIFICATIONS ($T_A = 25^{\circ}C$ unless otherwise noted) | | | | | | |
|--|---|---|------------------|-----|------|------|
| PARAMETER | | CONDITIONS | SYMBOL | ТҮР | MAX | UNIT |
| | MBR3035CT MBR3045CT | | | - | 0.70 | V |
| | MBR3050CT MBR3060CT | . I _F = 15A, T _J = 25°C | | - | 0.77 | V |
| | MBR3090CT MBR30100CT | | | - | 0.84 | V |
| | MBR30150CT | | | - | 0.95 | V |
| | MBR3035CT MBR3045CT | | | - | 0.82 | V |
| | MBR3050CT MBR3060CT | I _F = 30A, T _J = 25°C | | - | - | V |
| | MBR3090CT MBR30100CT | ··· ··· ··· ··· ······················ | | - | 0.94 | V |
| Forward voltage per | MBR30150CT | • | | - | 1.02 | V |
| diode ⁽¹⁾ | MBR3035CT MBR3045CT | | – V _F | - | 0.60 | V |
| | MBR3050CT MBR3060CT | l _F = 15A, T _J = 125°C | | - | 0.67 | V |
| | MBR3090CT MBR30100CT | | | - | 0.70 | V |
| | MBR30150CT | | | - | 0.92 | V |
| | MBR3035CT MBR3045CT | | | - | 0.73 | V |
| | MBR3050CT MBR3060CT | I _F = 30A, T _J = 125°C | | - | - | V |
| | MBR3090CT MBR30100CT | | | - | 0.82 | V |
| | MBR30150CT | | | - | 0.98 | V |
| Reverse current @ rated V_R per diode ⁽²⁾ | MBR3035CT MBR3045CT MBR3050CT MBR3060CT MBR3090CT MBR30100CT | T _J = 25°C | | - | 200 | μΑ |
| | MBR30150CT | | | - | 100 | μA |
| | MBR3035CT MBR3045CT | | I _R | - | 15 | mA |
| | MBR3050CT MBR3060CT | . T _J = 125°C | | - | 10 | mA |
| | MBR3090CT MBR30100CT | | | - | 7.5 | mA |
| | MBR30150CT | | | - | 5 | mA |



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Notes:

- 1. Pulse test with PW = 0.3ms
- 2. Pulse test with PW = 30ms

| ORDERING INFORMATION | | | |
|---------------------------------|----------|-----------|--|
| ORDERING CODE ⁽¹⁾⁽²⁾ | PACKAGE | PACKING | |
| MBR30xCT | TO-220AB | 50 / Tube | |
| MBR30xCTH | TO-220AB | 50 / Tube | |

Notes:

- 1. "x" defines voltage from 35V(MBR3035CT) to 150V(MBR30150CT)
- 2. "H" means AEC-Q101 qualified



INSTANTANEOUS REVERSE CURRENT (mA)

100

10

1

0.1

0.01

0.001

10

Fig.2 Typical Junction Capacitance

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CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

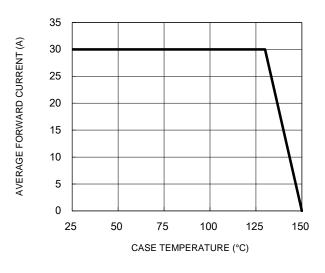


Fig.1 Forward Current Derating Curve

Fig.3 Typical Reverse Characteristics

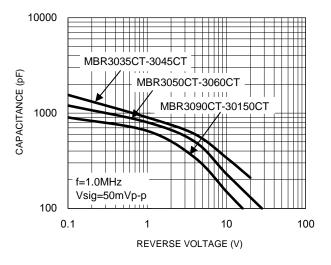
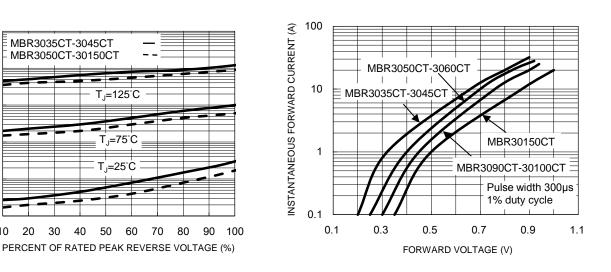


Fig.4 Typical Forward Characteristics



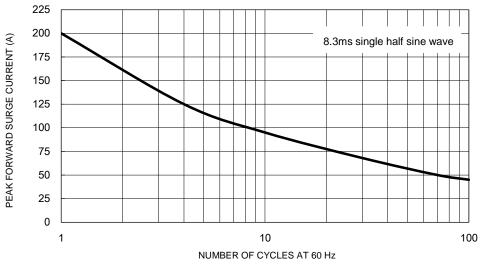


Fig.5 Maximum Non-Repetitive Forward Surge Current



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CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

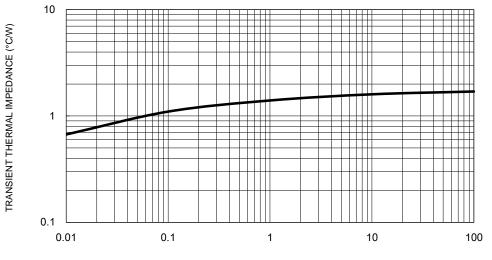


Fig.6 Typical Transient Thermal Impedance

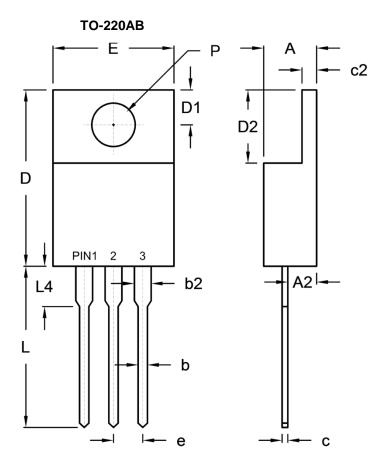
PULSE DURATION (s)



MBR3035CT - MBR30150CT

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PACKAGE OUTLINE DIMENSIONS



| DIM. | Unit (mm) | | Unit | (inch) | |
|------|-----------|-----------|-------|--------|--|
| | Min. | Min. Max. | | Max. | |
| A | 4.42 | 4.76 | 0.174 | 0.187 | |
| A2 | 2.20 | 2.80 | 0.087 | 0.110 | |
| b | 0.68 | 0.94 | 0.027 | 0.037 | |
| b2 | 1.14 | 1.77 | 0.045 | 0.070 | |
| с | 0.35 | 0.64 | 0.014 | 0.025 | |
| c2 | 1.14 | 1.40 | 0.045 | 0.055 | |
| D | 14.60 | 16.00 | 0.575 | 0.630 | |
| D1 | 2.62 | 3.44 | 0.103 | 0.135 | |
| D2 | 5.84 | 6.86 | 0.230 | 0.270 | |
| E | - | 10.50 | - | 0.413 | |
| е | 2.41 | 2.67 | 0.095 | 0.105 | |
| L | 13.19 | 14.79 | 0.519 | 0.582 | |
| L4 | 2.80 | 4.20 | 0.110 | 0.165 | |
| Р | 3.54 | 4.00 | 0.139 | 0.157 | |

MARKING DIAGRAM



| P/N | = Marking Code |
|-----|------------------|
| G | = Green Compound |
| YWW | = Date Code |
| F | = Factory Code |



MBR3035CT - MBR30150CT

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